Hark Hoe Tan

List of Publications by Year
in descending order

694	17,193	23879 60	37326 100
papers	citations	h-index	g-index

705	705	705	14174
all docs	docs citations	times ranked	citing authors

#	Article	IF	Citations
1	A New Strategy for Selective Area Growth of Highly Uniform InGaAs/InP Multiple Quantum Well Nanowire Arrays for Optoelectronic Device Applications. Advanced Functional Materials, 2022, 32, 2103057.	7.8	21
2	Semiconductor Nanowire Arrays for Highâ€Performance Miniaturized Chemical Sensing. Advanced Functional Materials, 2022, 32, 2107596.	7.8	16
3	Surfaceâ€Structured Cocatalyst Foils Unraveling a Pathway to Highâ€Performance Solar Water Splitting. Advanced Energy Materials, 2022, 12, 2102752.	10.2	11
4	Topical review: pathways toward cost-effective single-junction IIIâ€“V solar cells. Journal Physics D: Applied Physics, 2022, 55, 143002.	1.3	17
5	A hybrid random laser using dye with self-organized GaN nanorods. Semiconductor Science and Technology, 2022, 37, 025009.	1.0	2
6	Tuning the crystal structure and optical properties of selective area grown InGaAs nanowires. Nano Research, 2022, 15, 3695-3703.	5.8	5
7	Epitaxial Growth of GaAs Nanowires on Synthetic Mica by Metalâ€“Organic Chemical Vapor Deposition. ACS Applied Materials & Interfaces, 2022, 14, 3395-3403.	4.0	7
8	Protocol on the fabrication of monocrystalline thin semiconductor via crack-assisted layer exfoliation technique for photoelectrochemical water-splitting. STAR Protocols, 2022, 3, 101015.	0.5	1
9	The Australian National Fabrication Facility: Micro/nanotechnologies from Concept to Translation to End Users. Advanced Functional Materials, 2022, 32, .	7.8	0
10	A New Strategy for Selective Area Growth of Highly Uniform InGaAs/InP Multiple Quantum Well Nanowire Arrays for Optoelectronic Device Applications (Adv. Funct. Mater. 3/2022). Advanced Functional Materials, 2022, 32, .	7.8	1
11	Room-temperature optically detected magnetic resonance of single defects in hexagonal boron nitride. Nature Communications, 2022, 13, 618.	5.8	97
12	IIIâ€“V Semiconductor Whispering-Gallery Mode Micro-Cavity Lasers: Advances and Prospects. IEEE Journal of Quantum Electronics, 2022, 58, 1-18.	1.0	2
13	Investigation of lightâ€“matter interaction in single vertical nanowires in ordered nanowire arrays. Nanoscale, 2022, 14, 3527-3536.	2.8	6
14	Flexible InPâ€“ZnO nanowire heterojunction light emitting diodes. Nanoscale Horizons, 2022, 7, 446-454.	4.1	8
15	Design of InAs nanosheet arrays with ultrawide polarization-independent high absorption for infrared photodetection. Applied Physics Letters, 2022, 120, .	1.5	6
16	Ultrathin transparent metal capping layer on metal oxide carrier-selective contacts for Si solar cells. European Physical Journal: Special Topics, 2022, 231, 2933-2939.	1.2	2
17	nâ€SnO_x as a Transparent Electrode and Heterojunction for pâ€InP Nanowire Light Emitting Diodes. Advanced Optical Materials, 2022, 10, .	3.6	4
18	Recent Advances in Materials Design Using Atomic Layer Deposition for Energy Applications. Advanced Functional Materials, 2022, 32, .	7.8	34

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19	Direct GaAs Nanowire Growth and Monolithic Lightâ€Emitting Diode Fabrication on Flexible Plastic Substrates. Advanced Photonics Research, 2022, 3, .	1.7	4
20	Layer-by-Layer Assembly of CeO_{2â€“x}@C-rGO Nanocomposites and CNTs as a Multifunctional Separator Coating for Highly Stable Lithiumâ€“Sulfur Batteries. ACS Applied Materials & Interfaces, 2022, 14, 18634-18645.	4.0	24
21	Self-frequency-conversion nanowire lasers. Light: Science and Applications, 2022, 11, 120.	7.7	13
22	Nonpolar AlxGa1â^'xN/AlyGa1â^'yN multiple quantum wells on GaN nanowire for UV emission. Nano Research, 2022, 15, 7670-7680.	5.8	4
23	Deep-Ultraviolet Photodetectors Based on Hexagonal Boron Nitride Nanosheets Enhanced by Localized Surface Plasmon Resonance in Al Nanoparticles. ACS Applied Nano Materials, 2022, 5, 7481-7491.	2.4	9
24	Effective Passivation of InGaAs Nanowires for Telecommunication Wavelength Optoelectronics. Advanced Optical Materials, 2022, 10, .	3.6	5
25	Controlled Cracking for Large-Area Thin Film Exfoliation: Working Principles, Status, and Prospects. ACS Applied Electronic Materials, 2021, 3, 145-162.	2.0	10
26	Identifying carbon as the source of visible single-photon emission from hexagonal boron nitride. Nature Materials, 2021, 20, 321-328.	13.3	210
27	Controlled growth of porous oxygen-deficient NiCo₂O₄ nanobelts as high-efficiency electrocatalysts for oxygen evolution reaction. Catalysis Science and Technology, 2021, 11, 264-271.	2.1	11
28	Understanding the role of facets and twin defects in the optical performance of GaAs nanowires for laser applications. Nanoscale Horizons, 2021, 6, 559-567.	4.1	11
29	Passivation of InP solar cells using large area hexagonal-BN layers. Npj 2D Materials and Applications, 2021, 5, .	3.9	9
30	Earthâ€Abundant Amorphous Electrocatalysts for Electrochemical Hydrogen Production: A Review. Advanced Energy and Sustainability Research, 2021, 2, 2000071.	2.8	30
31	Electron-Selective Contact for GaAs Solar Cells. ACS Applied Energy Materials, 2021, 4, 1356-1364.	2.5	17
32	Nanomechanical behavior of single taper-free GaAs nanowires unravelled by in-situ TEM mechanical testing and molecular dynamics simulation. Materials Science & Engineering A: Structural Materials: Properties, Microstructure and Processing, 2021, 806, 140866.	2.6	4
33	Understanding Shape Evolution and Phase Transition in InP Nanostructures Grown by Selective Area Epitaxy. Small, 2021, 17, e2100263.	5.2	7
34	Managing Resonant and Nonresonant Lasing Modes in GaAs Nanowire Random Lasers. Nano Letters, 2021, 21, 3901-3907.	4.5	18
35	Postgrowth Shaping and Transport Anisotropy in Two-Dimensional InAs Nanofins. ACS Nano, 2021, 15, 7226-7236.	7.3	3
36	Ultralow Threshold, Single-Mode InGaAs/GaAs Multiquantum Disk Nanowire Lasers. ACS Nano, 2021, 15, 9126-9133.	7.3	19

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37	2D Carrier Localization at the Wurtzite-Zincblende Interface in Novel Layered InP Nanomembranes. ACS Photonics, 2021, 8, 1735-1745.	3.2	10
38	Terahertz Full-polarization-state Detection by Nanowires. , 2021, , .		0
39	Selective area epitaxy of IIIâ€“V nanostructure arrays and networks: Growth, applications, and future directions. Applied Physics Reviews, 2021, 8, .	5.5	75
40	Epitaxially Grown InP Micro-Ring Lasers. Nano Letters, 2021, 21, 5681-5688.	4.5	16
41	Thin silicon via crack-assisted layer exfoliation for photoelectrochemical water splitting. IScience, 2021, 24, 102921.	1.9	4
42	Surface-Tailored InP Nanowires via Self-Assembled Au Nanodots for Efficient and Stable Photoelectrochemical Hydrogen Evolution. Nano Letters, 2021, 21, 6967-6974.	4.5	13
43	Broadband GaAsSb Nanowire Array Photodetectors for Filter-Free Multispectral Imaging. Nano Letters, 2021, 21, 7388-7395.	4.5	36
44	Stable, multi-mode lasing in the strong localization regime from InP random nanowire arrays at low temperature. Optica, 2021, 8, 1160.	4.8	8
45	Manipulating Intermediates at the Auâ€“TiO₂ Interface over InP Nanopillar Array for Photoelectrochemical CO₂ Reduction. ACS Catalysis, 2021, 11, 11416-11428.	5.5	48
46	3D Tungsten Disulfide/Carbon Nanotube Networks as Separator Coatings and Cathode Additives for Stable and Fast Lithiumâ€“Sulfur Batteries. ACS Applied Materials & Interfaces, 2021, 13, 45547-45557.	4.0	17
47	Controlling the lasing modes in random lasers operating in the Anderson localization regime. Optics Express, 2021, 29, 33548.	1.7	7
48	Spatially dense integration of micron-scale devices from multiple materials on a single chip via transfer-printing. Optical Materials Express, 2021, 11, 3567.	1.6	17
49	Thermodynamic properties of metastable wurtzite InP nanosheets. Journal Physics D: Applied Physics, 2021, 54, 505112.	1.3	1
50	Selfâ€Powered InP Nanowire Photodetector for Singleâ€Photon Level Detection at Room Temperature. Advanced Materials, 2021, 33, e2105729.	11.1	18
51	Tunable Synthesis of 3D Niobium Oxynitride Nanosheets for Lithium-Ion Hybrid Capacitors with High Energy/Power Density. ACS Sustainable Chemistry and Engineering, 2021, 9, 14569-14578.	3.2	7
52	Effect of Au substrate and coating on the lasing characteristics of GaAs nanowires. Scientific Reports, 2021, 11, 21378.	1.6	5
53	Role of defects and grain boundaries in the thermal response of wafer-scale hBN films. Nanotechnology, 2021, 32, 075702.	1.3	6
54	Epitaxially-grown InP micro-ring lasers. , 2021, , .		0

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55	Anderson localization of light in InP nanowires for stable, multimode lasing. , 2021, , .		0
56	Non-epitaxial carrier selective contacts for III-V solar cells: A review. Applied Materials Today, 2020, 18, 100503.	2.3	23
57	Fabrication of WO3/TiO2 core-shell nanowire arrays: Structure design and high electrochromic performance. Electrochimica Acta, 2020, 330, 135189.	2.6	34
58	Engineering IIIâ€“V Semiconductor Nanowires for Device Applications. Advanced Materials, 2020, 32, e1904359.	11.1	43
59	Forward and Backward Switching of Nonlinear Unidirectional Emission from GaAs Nanoantennas. ACS Nano, 2020, 14, 1379-1389.	7.3	53
60	Monocrystalline InP Thin Films with Tunable Surface Morphology and Energy Band gap. ACS Applied Materials & Interfaces, 2020, 12, 36380-36388.	4.0	12
61	Solar Water Splitting: Over 17% Efficiency Standâ€Alone Solar Water Splitting Enabled by Perovskiteâ€Silicon Tandem Absorbers (Adv. Energy Mater. 28/2020). Advanced Energy Materials, 2020, 10, 2070122.	10.2	4
62	Theoretical Insights into the Favorable Functionalized Ti₂C-Based MXenes for Lithiumâ€“Sulfur Batteries. ACS Omega, 2020, 5, 29272-29283.	1.6	28
63	Three-Dimensional Ordered Macroporous TiO₂â€“TaO_xN_y Heterostructure for Photoelectrochemical Water Splitting. Journal of Physical Chemistry C, 2020, 124, 24135-24144.	1.5	4
64	Hole and Electron Effective Masses in Single InP Nanowires with a Wurtzite-Zincblende Homojunction. ACS Nano, 2020, 14, 11613-11622.	7.3	8
65	Impact of invasive metal probes on Hall measurements in semiconductor nanostructures. Nanoscale, 2020, 12, 20317-20325.	2.8	4
66	Facet-dependent growth of InAsP quantum wells in InP nanowire and nanomembrane arrays. Nanoscale Horizons, 2020, 5, 1530-1537.	4.1	8
67	Electrical Properties of Compact Drop-Casted Cu2SnS3 Films. Journal of Electronic Materials, 2020, 49, 6403-6409.	1.0	1
68	Facet-Related Non-uniform Photoluminescence in Passivated GaAs Nanowires. Frontiers in Chemistry, 2020, 8, 607481.	1.8	2
69	Carbon-Coated Self-Assembled Ultrathin T-Nb₂O₅ Nanosheets for High-Rate Lithium-Ion Storage with Superior Cycling Stability. ACS Applied Energy Materials, 2020, 3, 12037-12045.	2.5	26
70	Over 17% Efficiency Standâ€Alone Solar Water Splitting Enabled by Perovskiteâ€Silicon Tandem Absorbers. Advanced Energy Materials, 2020, 10, 2000772.	10.2	58
71	Highly regular rosette-shaped cathodoluminescence in GaN self-assembled nanodisks and nanorods. Nano Research, 2020, 13, 2500-2505.	5.8	6
72	Polarizationâ€Independent Indium Phosphide Nanowire Photodetectors. Advanced Optical Materials, 2020, 8, 2000514.	3.6	9

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73	In situ passivation of GaAsSb nanowires for enhanced infrared photoresponse. Nanotechnology, 2020, 31, 244002.	1.3	13
74	Review on III-V Semiconductor Single Nanowire-Based Room Temperature Infrared Photodetectors. Materials, 2020, 13, 1400.	1.3	44
75	Rational Design of Oxygen Deficiency-Controlled Tungsten Oxide Electrochromic Films with an Exceptional Memory Effect. ACS Applied Materials & Interfaces, 2020, 12, 32658-32665.	4.0	46
76	Cathodoluminescence visualisation of local thickness variations of GaAs/AlGaAs quantum-well tubes on nanowires. Nanotechnology, 2020, 31, 424001.	1.3	4
77	Characterization, Selection, and Microassembly of Nanowire Laser Systems. Nano Letters, 2020, 20, 1862-1868.	4.5	17
78	Highly uniform InGaAs/InP quantum well nanowire array-based light emitting diodes. Nano Energy, 2020, 71, 104576.	8.2	23
79	Improving the Morphology and Crystal Quality of AlN Grown on Two-Dimensional hBN. Crystal Growth and Design, 2020, 20, 1811-1819.	1.4	7
80	IIIâ€“V Semiconductor Materials for Solar Hydrogen Production: Status and Prospects. ACS Energy Letters, 2020, 5, 611-622.	8.8	54
81	Design of Ultrathin InP Solar Cell Using Carrier Selective Contacts. IEEE Journal of Photovoltaics, 2020, 10, 1657-1666.	1.5	18
82	Three-dimensional cross-nanowire networks recover full terahertz state. Science, 2020, 368, 510-513.	6.0	81
83	Exploring the band structure of Wurtzite InAs nanowires using photocurrent spectroscopy. Nano Research, 2020, 13, 1586-1591.	5.8	7
84	Structure modulated amorphous/crystalline WO3 nanoporous arrays with superior electrochromic energy storage performance. Solar Energy Materials and Solar Cells, 2020, 212, 110579.	3.0	45
85	Carrier dynamics and recombination mechanisms in InP twinning superlattice nanowires. Optics Express, 2020, 28, 16795.	1.7	7
86	Wavelength-tunable InAsP quantum dots in InP nanowires. Applied Physics Letters, 2019, 115, 053101.	1.5	7
87	Effect of Sn Addition on Epitaxial GaAs Nanowire Grown at Different Temperatures in Metalâ€“Organic Chemical Vapor Deposition. Crystal Growth and Design, 2019, 19, 5314-5319.	1.4	4
88	Strong Hot Carrier Effects in Single Nanowire Heterostructures. Nano Letters, 2019, 19, 5062-5069.	4.5	13
89	On the origin of dislocation generation and annihilation in Î± -Ga2O3 epilayers on sapphire. Applied Physics Letters, 2019, 115, .	1.5	37
90	Band alignment and band bending at Î±-Ga2O3/ZnO n-n isotype hetero-interface. Applied Physics Letters, 2019, 115, .	1.5	25

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91	Understanding the Effect of Catalyst Size on the Epitaxial Growth of Hierarchical Structured InGaP Nanowires. Nano Letters, 2019, 19, 8262-8269.	4.5	4
92	Nanowire Quantum Dot Surface Engineering for High Temperature Single Photon Emission. ACS Nano, 2019, 13, 13492-13500.	7.3	22
93	Second-Harmonic Generation in (111) Gallium Arsenide Nanoantennas. , 2019, , .		0
94	High-Efficiency Solar Cells from Extremely Low Minority Carrier Lifetime Substrates Using Radial Junction Nanowire Architecture. ACS Nano, 2019, 13, 12015-12023.	7.3	31
95	Crystalline WO3 nanowires array sheathed with sputtered amorphous shells for enhanced electrochromic performance. Applied Surface Science, 2019, 498, 143796.	3.1	42
96	Resonant harmonic generation in AlGaAs nanoantennas probed by cylindrical vector beams. Nanoscale, 2019, 11, 1745-1753.	2.8	26
97	Four-Dimensional Probing of Phase-Reaction Dynamics in Au/GaAs Nanowires. Nano Letters, 2019, 19, 781-786.	4.5	3
98	Design Principles for Fabrication of InP-Based Radial Junction Nanowire Solar Cells Using an Electron Selective Contact. IEEE Journal of Photovoltaics, 2019, 9, 980-991.	1.5	31
99	Introduction of TiO₂ in CuI for Its Improved Performance as a p-Type Transparent Conductor. ACS Applied Materials & Interfaces, 2019, 11, 24254-24263.	4.0	33
100	Regaining a Spatial Dimension: Mechanically Transferrable Two-Dimensional InAs Nanofins Grown by Selective Area Epitaxy. Nano Letters, 2019, 19, 4666-4677.	4.5	25
101	Realization of p-type gallium nitride by magnesium ion implantation for vertical power devices. Scientific Reports, 2019, 9, 8796.	1.6	24
102	InGaAsP as a Promising Narrow Band Gap Semiconductor for Photoelectrochemical Water Splitting. ACS Applied Materials & Interfaces, 2019, 11, 25236-25242.	4.0	21
103	Shape Engineering of InP Nanostructures by Selective Area Epitaxy. ACS Nano, 2019, 13, 7261-7269.	7.3	41
104	Multiwavelength Single Nanowire InGaAs/InP Quantum Well Light-Emitting Diodes. Nano Letters, 2019, 19, 3821-3829.	4.5	32
105	Tailoring Second-Harmonic Emission from (111)-GaAs Nanoantennas. Nano Letters, 2019, 19, 3905-3911.	4.5	66
106	Mechanical Behavior of InP Twinning Superlattice Nanowires. Nano Letters, 2019, 19, 4490-4497.	4.5	18
107	Compositional Varied Coreâ€“Shell InGaP Nanowires Grown by Metalâ€“Organic Chemical Vapor Deposition. Nano Letters, 2019, 19, 3782-3788.	4.5	17
108	Unusual spin properties of InP wurtzite nanowires revealed by Zeeman splitting spectroscopy. Physical Review B, 2019, 99, .	1.1	14

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109	Nanosails Showcasing Zn₃As₂ as an Optoelectronicâ€Grade Earth Abundant Semiconductor. Physica Status Solidi - Rapid Research Letters, 2019, 13, 1900084.	1.2	8
110	Ultrathin Ta₂O₅ electron-selective contacts for high efficiency InP solar cells. Nanoscale, 2019, 11, 7497-7505.	2.8	38
111	Unexpected benefits of stacking faults on the electronic structure and optical emission in wurtzite GaAs/GaInP core/shell nanowires. Nanoscale, 2019, 11, 9207-9215.	2.8	18
112	Ultrasensitive Mid-wavelength Infrared Photodetection Based on a Single InAs Nanowire. ACS Nano, 2019, 13, 3492-3499.	7.3	45
113	Electron selective contact for high efficiency core-shell nanowire solar cell. , 2019, , .		4
114	Engineering the Side Facets of Vertical [100] Oriented InP Nanowires for Novel Radial Heterostructures. Nanoscale Research Letters, 2019, 14, 399.	3.1	9
115	Threshold reduction and yield improvement of semiconductor nanowire lasers via processing-related end-facet optimization. Nanoscale Advances, 2019, 1, 4393-4397.	2.2	9
116	Axial pâ€•n junction design and characterization for InP nanowire array solar cells. Progress in Photovoltaics: Research and Applications, 2019, 27, 237-244.	4.4	22
117	Solutionâ€Processed InAs Nanowire Transistors as Microwave Switches. Advanced Electronic Materials, 2019, 5, 1800323.	2.6	3
118	Optical Study of p-Doping in GaAs Nanowires for Low-Threshold and High-Yield Lasing. Nano Letters, 2019, 19, 362-368.	4.5	24
119	Broadband Metamaterial Absorbers. Advanced Optical Materials, 2019, 7, 1800995.	3.6	404
120	Engineering IIIâ€“V Nanowires for Optoelectronics: From Visible to Terahertz. , 2019, , .		0
121	Enhancement of radiation tolerance in GaAs/AlGaAs coreâ€“shell and InP nanowires. Nanotechnology, 2018, 29, 225703.	1.3	8
122	Transfer printing of semiconductor nanowire lasers. IET Optoelectronics, 2018, 12, 30-35.	1.8	7
123	Photo-assisted synthesis of coaxial-structured polypyrrole/electrochemically hydrogenated TiO2 nanotube arrays as a high performance supercapacitor electrode. RSC Advances, 2018, 8, 13393-13400.	1.7	10
124	Temperature effects in contacts between a metal and a semiconductor nanowire near the degenerate doping. Nanotechnology, 2018, 29, 165202.	1.3	1
125	Electrochemical hydrogenation of mixed-phase TiO2 nanotube arrays enables remarkably enhanced photoelectrochemical water splitting performance. Science Bulletin, 2018, 63, 194-202.	4.3	30
126	In situ mechanical resonance behaviour of pristine and defective zinc blende GaAs nanowires. Nanoscale, 2018, 10, 2588-2595.	2.8	15

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127	Reducing Zn diffusion in single axial junction InP nanowire solar cells for improved performance. Progress in Natural Science: Materials International, 2018, 28, 178-182.	1.8	23
128	Tantalum Oxide Electron-Selective Heterocontacts for Silicon Photovoltaics and Photoelectrochemical Water Reduction. ACS Energy Letters, 2018, 3, 125-131.	8.8	127
129	CuI-TiO2Composite Thin Film for Flexible Electronic Applications. , 2018, , .		1
130	Precise Positioning and Orientation of Nanowire Lasers in Regular and Patterned Surfaces. , 2018, , .		2
131	Room Temperature GaAsSb Array Photodetectors. , 2018, , .		1
132	The Route to Nanoscale Terahertz Technology: Nanowire-based Terahertz Detectors and Terahertz Modulators. , 2018, , .		0
133	Radial Growth Evolution of InGaAs/InP Multi-Quantum-Well Nanowires Grown by Selective-Area Metal Organic Vapor-Phase Epitaxy. ACS Nano, 2018, 12, 10374-10382.	7.3	26
134	Preparation of V₂O₅ dot-decorated WO₃ nanorod arrays for high performance multi-color electrochromic devices. Journal of Materials Chemistry C, 2018, 6, 12206-12216.	2.7	31
135	The effect of Sn addition on GaAs nanowire grown by vaporâ€“liquidâ€“solid growth mechanism. Nanotechnology, 2018, 29, 465601.	1.3	4
136	Vertically Emitting Indium Phosphide Nanowire Lasers. Nano Letters, 2018, 18, 3414-3420.	4.5	33
137	The effect of nitridation on the polarity and optical properties of GaN self-assembled nanorods. Nanoscale, 2018, 10, 11205-11210.	2.8	9
138	IIIâ€“V Semiconductor Single Nanowire Solar Cells: A Review. Advanced Materials Technologies, 2018, 3, 1800005.	3.0	75
139	Role of surface energy in nanowire growth. Journal Physics D: Applied Physics, 2018, 51, 283002.	1.3	33
140	Indium phosphide based solar cell using ultra-thin ZnO as an electron selective layer. Journal Physics D: Applied Physics, 2018, 51, 395301.	1.3	28
141	Flow modulation epitaxy of hexagonal boron nitride. 2D Materials, 2018, 5, 045018.	2.0	57
142	Identification and modulation of electronic band structures of single-phase Î²-(AlxGa1â^'x)2O3 alloys grown by laser molecular beam epitaxy. Applied Physics Letters, 2018, 113, .	1.5	43
143	Modal refractive index measurement in nanowire lasersâ€”a correlative approach. Nano Futures, 2018, 2, 035004.	1.0	8
144	Tailored Emission Properties of ZnTe/ZnTe:O/ZnO Coreâ€“Shell Nanowires Coupled with an Al Plasmonic Bowtie Antenna Array. ACS Nano, 2018, 12, 7327-7334.	7.3	8

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145	Engineering III-V nanowires for optoelectronics: from epitaxy to terahertz photonics. , 2018, , .		0
146	Radiation effects on GaAs/AlGaAs core/shell ensemble nanowires and nanowire infrared photodetectors. Nanotechnology, 2017, 28, 125702.	1.3	14
147	Single n⁺-i-n⁺InP nanowires for highly sensitive terahertz detection. Nanotechnology, 2017, 28, 125202.	1.3	26
148	Nonlinear Optical Magnetism Revealed by Second-Harmonic Generation in Nanoantennas. Nano Letters, 2017, 17, 3914-3918.	4.5	100
149	Growth and optical properties of In x Ga1â^'x P nanowires synthesized by selective-area epitaxy. Nano Research, 2017, 10, 672-682.	5.8	24
150	3D Atomic-Scale Insights into Anisotropic Core-Shell-Structured InGaAs Nanowires Grown by Metal-Organic Chemical Vapor Deposition. Advanced Materials, 2017, 29, 1701888.	11.1	15
151	The influence of surfaces on the transient terahertz conductivity and electron mobility of GaAs nanowires. Journal Physics D: Applied Physics, 2017, 50, 224001.	1.3	31
152	Strong Amplified Spontaneous Emission from High Quality GaAs_{1â€“x}Sb_x Single Quantum Well Nanowires. Journal of Physical Chemistry C, 2017, 121, 8636-8644.	1.5	15
153	Choice of Polymer Matrix for a Fast Switchable IIIâ€“V Nanowire Terahertz Modulator. MRS Advances, 2017, 2, 1475-1480.	0.5	1
154	An Ultrafast Switchable Terahertz Polarization Modulator Based on IIIâ€“V Semiconductor Nanowires. Nano Letters, 2017, 17, 2603-2610.	4.5	77
155	Hybrid Nanowire Ion-to-Electron Transducers for Integrated Bioelectronic Circuitry. Nano Letters, 2017, 17, 827-833.	4.5	26
156	Semiconductor nanowires in terahertz photonics: From spectroscopy to ultrafast nanowire-based devices. , 2017, , .		0
157	Dopantâ€Free Twinning Superlattice Formation in InSb and InP Nanowires. Physica Status Solidi - Rapid Research Letters, 2017, 11, 1700310.	1.2	15
158	The influence of atmosphere on the performance of pure-phase WZ and ZB InAs nanowire transistors. Nanotechnology, 2017, 28, 454001.	1.3	14
159	Chiral Metamaterials: A Terahertz Controlledâ€NOT Gate Based on Asymmetric Rotation of Polarization in Chiral Metamaterials (Advanced Optical Materials 18/2017). Advanced Optical Materials, 2017, 5, .	3.6	0
160	Extreme absorption enhancement in ZnTe:O/ZnO intermediate band core-shell nanowires by interplay of dielectric resonance and plasmonic bowtie nanoantennas. Scientific Reports, 2017, 7, 7503.	1.6	12
161	Integration of Semiconductor Nanowire Lasers with Polymeric Waveguide Devices on a Mechanically Flexible Substrate. Nano Letters, 2017, 17, 5990-5994.	4.5	55
162	Impurity Free Vacancy Disordering (IFVD) of InGaAs/AlGaAs Quantum Well Laser Structures. ECS Journal of Solid State Science and Technology, 2017, 6, N122-N126.	0.9	0

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163	Large-Scale Statistics for Threshold Optimization of Optically Pumped Nanowire Lasers. Nano Letters, 2017, 17, 4860-4865.	4.5	31
164	A Terahertz Controlledâ€NOT Gate Based on Asymmetric Rotation of Polarization in Chiral Metamaterials. Advanced Optical Materials, 2017, 5, 1700108.	3.6	15
165	InPâ€“In_xGa_{1â^'x}As core-multi-shell nanowire quantum wells with tunable emission in the 1.3â€“1.55 Î¼m wavelength range. Nanoscale, 2017, 9, 13554-13562.	2.8	9
166	Engineering the Photoresponse of InAs Nanowires. ACS Applied Materials & Interfaces, 2017, 9, 43993-44000.	4.0	49
167	Dynamics and control of gold-encapped gallium arsenide nanowires imaged by 4D electron microscopy. Proceedings of the National Academy of Sciences of the United States of America, 2017, 114, 12876-12881.	3.3	13
168	Electrochemical hydrogenated TiO₂nanotube arrays decorated with 3D cotton-like porous MnO₂enables superior supercapacitive performance. RSC Advances, 2017, 7, 31512-31518.	1.7	6
169	Critical Temperature for the Conversion from Wurtzite to Zincblende of the Optical Emission of InAs Nanowires. Journal of Physical Chemistry C, 2017, 121, 16650-16656.	1.5	2
170	Broadband Single-Nanowire Photoconductive Terahertz Detectors. , 2017, , .		0
171	GaAs/AlGaAs core-shell ensemble nanowire photodetectors. , 2017, , .		0
172	Modulation of Terahertz Polarization on Picosecond Timescales using Polymer-Encapsulated Semiconductor Nanowires. , 2017, , .		0
173	Robust Subâ€Monolayers of Co₃O₄ Nanoâ€Islands: A Highly Transparent Morphology for Efficient Water Oxidation Catalysis. Advanced Energy Materials, 2016, 6, 1600697.	10.2	44
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